

SST4416A N-CHANNEL JFET



Linear Systems replaces discontinued Siliconix SST4416A The SST4416A is a N-Channel high frequency JFET amplifier

The SST4416A N-channel JFET is designed to provide high-performance amplification at high frequencies.

The SOT-23 package provides ease of manufacturing, and a lower cost assembly option.

SST4416A Benefits:

- Wideband High Gain
- Very High System Sensitivity
- High Quality of Amplification
- High-Speed Switching Capability
- High Low-Level Signal Amplification

SST4416A Applications:

- High-Frequency Amplifier / Mixer
- Oscillator
- Sample-and-Hold
- Very Low Capacitance Switches

FEATURES					
DIRECT REPLACEMENT FOR SILICONIX SST4416A					
EXCEPTIONAL GAIN (400 MHz)	10dB (min)				
VERY LOW NOISE FIGURE (400 MHz) 4dB (max)					
VERY LOW DISTORTION					
HIGH AC/DC SWITCH OFF-ISOLATION					
ABSOLUTE MAXIMUM RATINGS					
@ 25°C (unless otherwise noted)					
Maximum Temperatures					
Storage Temperature	-65°C to +200°C				
Operating Junction Temperature	-55°C to +135°C				
Maximum Power Dissipation					
Continuous Power Dissipation	300mW				
MAXIMUM CURRENT					
Gate Current (Note 1)	10mA				
MAXIMUM VOLTAGES					
Gate to Drain or Gate to Source	-35V				

SST4416A ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	MIN	TYP.	MAX	UNITS	CONDITIONS	
BV_{GSS}	Gate to Source Breakdown Voltage	-35			V	$I_{G} = -1\mu A$, $V_{DS} = 0V$	
$V_{GS(off)}$	Gate to Source Cutoff Voltage	-2.5		-6	V	$V_{DS} = 15V, I_{D} = 1nA$	
I _{DSS}	Gate to Source Saturation Current	5	4-	1 5	mA	$V_{DS} = 15V, V_{GS} = 0V$	
I _{GSS}	Gate <mark>Le</mark> akage Current			-0.1	nA	$V_{GS} = -20V, V_{DS} = 0V$	
g _{fs}	Forward <mark>T</mark> rans <mark>co</mark> nd <mark>uc</mark> tance	4500		750 <mark>0</mark>	μS	$V_{DS} = 15V, V_{GS} = 0V, f = 1kHz$	
g _{os}	Outp <mark>ut</mark> Con <mark>d</mark> uct <mark>an</mark> ce			50	μS		
C _{iss}	Input Capacitance ²			0.8	pF		
C_{rss}	Reverse Transfer Capacitance ²			4	pF	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	
C _{oss}	Output Capacitance ²			2	pF		
e _n	Equivalent Input Noise Voltage		6		nV/√Hz	$V_{DS} = 10V$, $V_{GS} = 0V$, $f = 1kHz$	

SST4416A HIGH FREQUENCY ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTIC	100 Mhz 40		400 [Mhz	UNITS	CONDITIONS
		MIN	MAX	MIN	MAX		
g _{Iss}	Input Conductance		100		1000		
b _{Iss}	Input Susceptance ²		2500		10000	c	$V_{DS} = 15V, V_{GS} = 0V$
g _{oss}	Output Conductance		75		100	μS	V _{DS} = 13V, V _{GS} = 0V
b _{oss}	Output Susceptance ²		1000		4000		
G _{fs}	Forward Transconductance			4000			
G_{ps}	Power Gain ²	18		10		dB	$V_{DS} = 15V$, $I_D = 5mA$
NF	Noise Figure ²		2		4		$V_{DS} = 15V$, $I_D = 5mA$, $R_G = 1k\Omega$
NOTES	1 . Absolute maximum ratings are limiting values above which SST4416A serviceability may be impaired.						

2. Not production tested, guaranteed by design

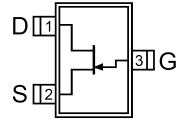
Micross Components Europe



Available Packages:

SST4416A in SOT-23 SST4416A in bare die.

SOT-23 (Top View)



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